CLAIMS

1. A resist pattern forming method, which comprises applying a positive resist composition comprising a resin component (A), which has an alkali-soluble unit content of less than 20 mol% and also has an acid dissociable dissolution inhibiting group, alkali solubility thereof being enhanced by action of acid, an acid generator component (B) which generates an acid under exposure, and an organic solvent (C) which dissolves the components (A) and (B) on a substrate; subjecting the resulting film to prebaking, selective exposure, post exposure baking and alkali development; performing a displacing step of displacing a liquid existing on the substrate with a displacing liquid at least one time; displacing the displacing liquid with a liquid for critical drying; and performing a drying step of drying the liquid for critical drying via a critical state.

2. The resist pattern forming method according to claim 1, wherein the displacing step is performed after the alkali development and the subsequent water rinsing.

3. The resist pattern forming method according to claim 1, wherein, in the displacing step, an operation of displacing the liquid existing on the substrate with a displacing liquid

containing a surfactant is performed at least one time.

4. The resist pattern forming method according to claim 1, wherein an inert fluorine liquid is used as the displacing liquid.

5. The resist pattern forming method according to claim 1, wherein, in the displacing step, the liquid existing on the substrate is displaced with a first displacing liquid, and furthermore, the liquid existing on the substrate is displaced with a second displacing liquid.

6. The resist pattern forming method according to claim 1, wherein the exposure is performed using a KrF excimer laser.

7. The resist pattern forming method according to claim 1, wherein the exposure is performed using an ArF excimer laser.

8. The resist pattern forming method according to claim 1, wherein the exposure is performed using an electron beam.

9. A resist pattern obtained by the resist pattern forming method according to claim 1.

10. The resist pattern according to claim 9, which has a line

width of 20 to 130 nm, an aspect ratio of 2.0 to 10.0 and a pitch of 40 to 300 nm.